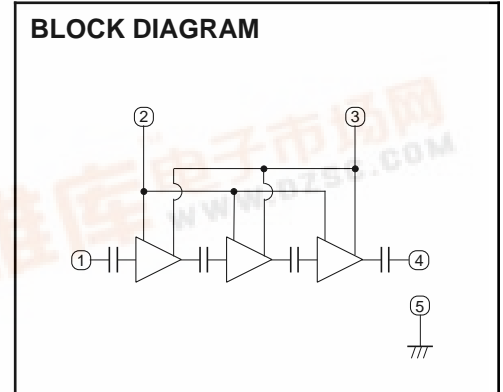
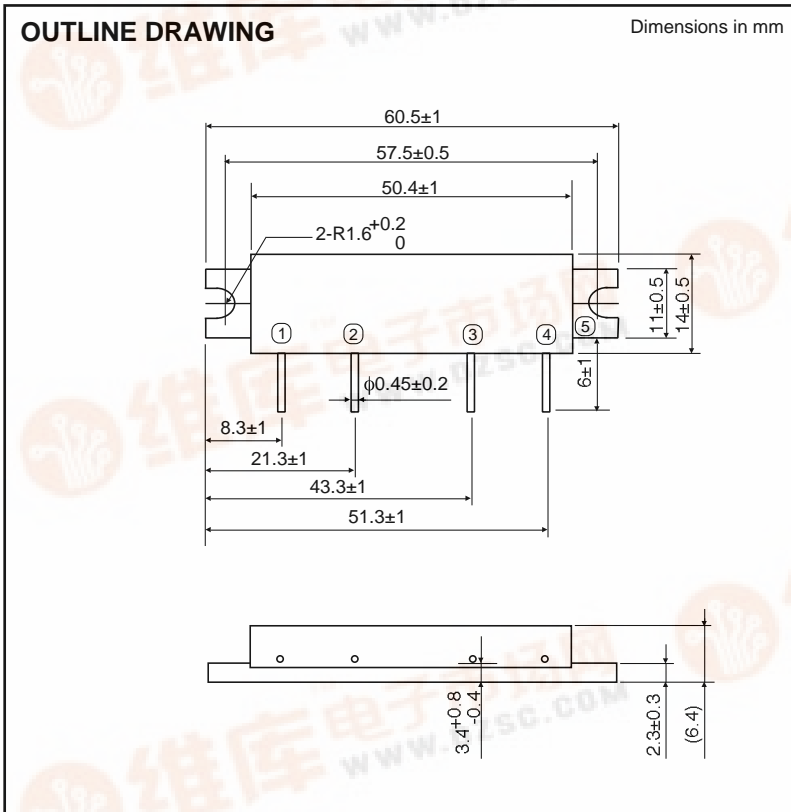


MITSUBISHI RF POWER MODULE

M68701

SILICON MOS FET POWER AMPLIFIER, 820-851MHz, 6W, FM PORTABLE RADIO



PIN:

- ① Pin : RF INPUT
- ② V_{GG} : GATE BIAS SUPPLY
- ③ V_{DD} : DRAIN BIAS SUPPLY
- ④ P_o : RF OUTPUT
- ⑤ GND: FIN

ABSOLUTE MAXIMUM RATINGS (T_c=25°C unless otherwise noted)

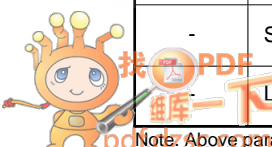
Symbol	Parameter	Conditions	Ratings	Unit
V _{DD}	Supply voltage	V _{GG} 3.5V, Z _G =Z _L =50	17	V
V _{GG}	Gate bias voltage		5.5	V
P _{in}	Input power	f=820-851MHz, Z _G =Z _L =50	10	mW
P _o	Output power	f=820-851MHz, Z _G =Z _L =50	10	W
T _c (OP)	Operation case temperature	f=820-851MHz, Z _G =Z _L =50	-30 to +100	°C
T _{stg}	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (T_c=25°C, Z_G=Z_L=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min	Max		
f	Frequency range		820	851	MHz	
P _o	Output power	V _{DD} =12.5V, V _{GG} =5V, P _{in} =1mW	6		W	
τ	Total efficiency		35		%	
2f _o	2nd. harmonic			-30		dBc
in	Input VSWR			4		-
-	Stability	Z _G =Z _L =50, V _{DD} =10-16V, Load VSWR<4:1	No parasitic oscillation		-	
-	Load VSWR tolerance	V _{DD} =15.2V, P _{in} =1mW, P _o =6W (V _{GG} adjust), Z _L =20:1	No degradation or destroy		-	

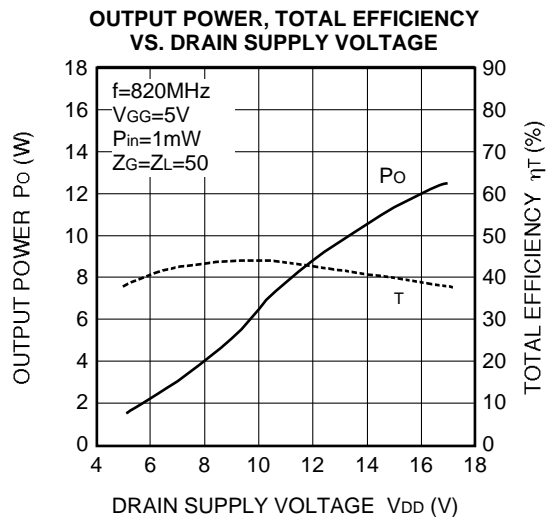
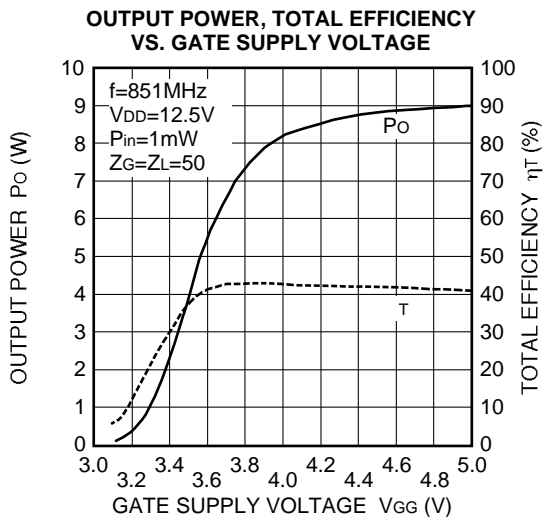
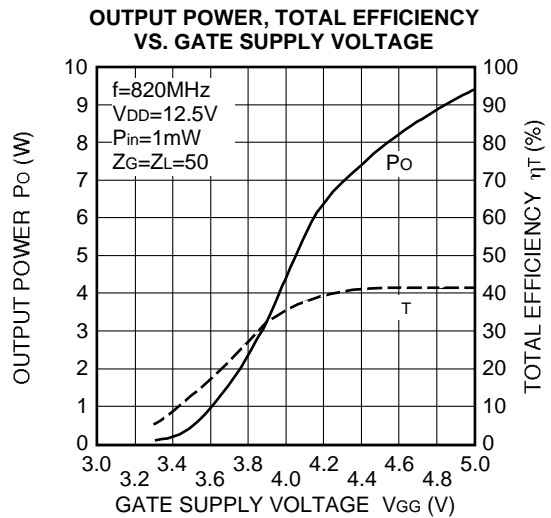
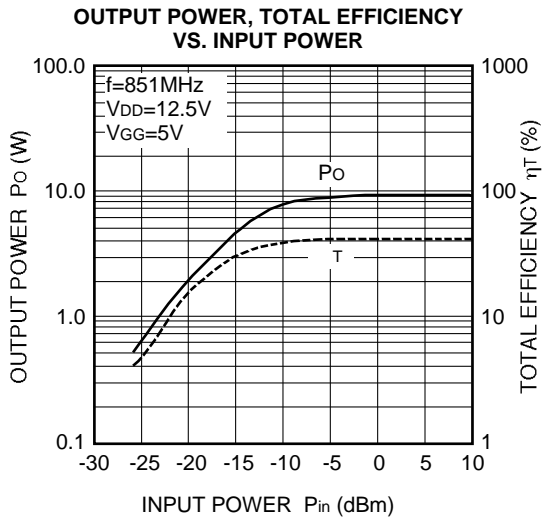
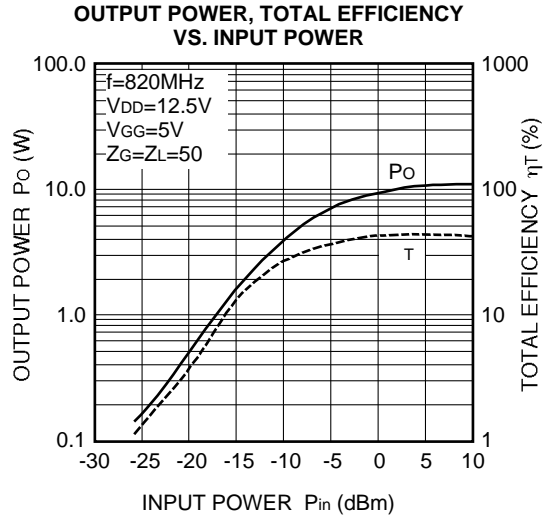
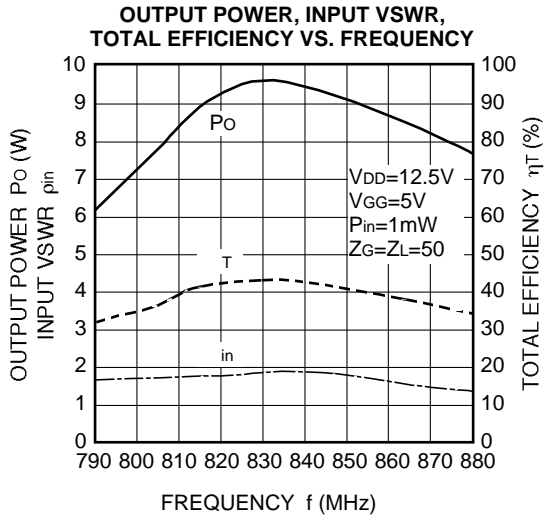
Note. Above parameters, ratings, limits and test conditions are subject to change.



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TYPICAL PERFORMANCE DATA



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